



# FGH80N60FD2

## 600V, 80A Field Stop IGBT

### Features

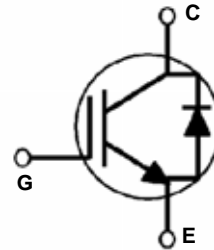
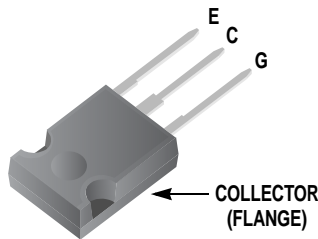
- High current capability
- Low saturation voltage:  $V_{CE(sat)} = 1.8V @ I_C = 40A$
- High input impedance
- Fast switching
- RoHS compliant

### General Description

Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop IGBTs offer the optimum performance for Induction Heating applications where low conduction and switching losses are essential.

### Applications

- Induction Heating Application



### Absolute Maximum Ratings

Symbol	Description	Ratings	Units
$V_{CES}$	Collector-Emitter Voltage	600	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ C$	80	A
	Collector Current @ $T_C = 100^\circ C$	40	A
$I_{CM} (1)$	Pulsed Collector Current @ $T_C = 25^\circ C$	160	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ C$	290	W
	Maximum Power Dissipation @ $T_C = 100^\circ C$	116	W
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ C$
$T_L$	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ C$

**Notes :**

(1) Repetitive rating : Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction-to-Case	--	0.43	$^\circ C/W$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction-to-Case	--	1.45	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ C/W$

### Package Marking and Ordering Information

Device Marking	Device	Package	Packaging Type	Qty per Tube	Max Qty per Box
FGH80N60FD2	FGH80N60FD2TU	TO-247	Tube	30ea	-

### Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
<b>Off Characteristics</b>						
$V_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	--	0.6	--	V/°C
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	$\mu A$
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 400$	nA
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\mu A, V_{CE} = V_{GE}$	4.5	5.5	7.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40A, V_{GE} = 15V$	--	1.8	2.4	V
		$I_C = 40A, V_{GE} = 15V, T_C = 125^\circ C$	--	2.05	--	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V, f = 1MHz$	--	2110	--	pF
$C_{oes}$	Output Capacitance		--	200	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	60	--	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400V, I_C = 40A, R_G = 10\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 25^\circ C$	--	21	--	ns
$t_r$	Rise Time		--	56	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	126	--	ns
$t_f$	Fall Time		--	50	100	ns
$E_{on}$	Turn-On Switching Loss		--	1	1.5	mJ
$E_{off}$	Turn-Off Switching Loss		--	0.52	0.78	mJ
$E_{ts}$	Total Switching Loss	--	1.52	2.28	mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400V, I_C = 40A, R_G = 10\Omega, V_{GE} = 15V, \text{Inductive Load}, T_C = 125^\circ C$	--	20	--	ns
$t_r$	Rise Time		--	54	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	131	--	ns
$t_f$	Fall Time		--	70	--	ns
$E_{on}$	Turn-On Switching Loss		--	1.1	--	mJ
$E_{off}$	Turn-Off Switching Loss		--	0.78	--	mJ
$E_{ts}$	Total Switching Loss	--	1.88	--	mJ	
$Q_g$	Total Gate Charge	$V_{CE} = 400V, I_C = 40A, V_{GE} = 15V$	--	120	--	nC
$Q_{ge}$	Gate-Emitter Charge		--	14	--	nC
$Q_{gc}$	Gate-Collector Charge		--	58	--	nC

**Electrical Characteristics of the Diode** T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Units	
V <sub>FM</sub>	Diode Forward Voltage	I <sub>F</sub> = 15A	T <sub>C</sub> = 25°C	-	1.2	1.5	V
			T <sub>C</sub> = 125°C	-	1.0	-	
t <sub>rr</sub>	Diode Reverse Recovery Time	I <sub>ES</sub> = 15A, dI <sub>ES</sub> /dt = 200A/μs	T <sub>C</sub> = 25°C	-	61	-	ns
			T <sub>C</sub> = 125°C	-	125	-	
I <sub>rr</sub>	Diode Reverse Recovery Current	I <sub>ES</sub> = 15A, dI <sub>ES</sub> /dt = 200A/μs	T <sub>C</sub> = 25°C	-	4.8	-	ns
			T <sub>C</sub> = 125°C	-	8.4	-	
Q <sub>rr</sub>	Diode Reverse Recovery Charge	I <sub>ES</sub> = 15A, dI <sub>ES</sub> /dt = 200A/μs	T <sub>C</sub> = 25°C	-	146	-	nC
			T <sub>C</sub> = 125°C	-	525	-	

## Typical Performance Characteristics

Figure 1. Typical Output Characteristics

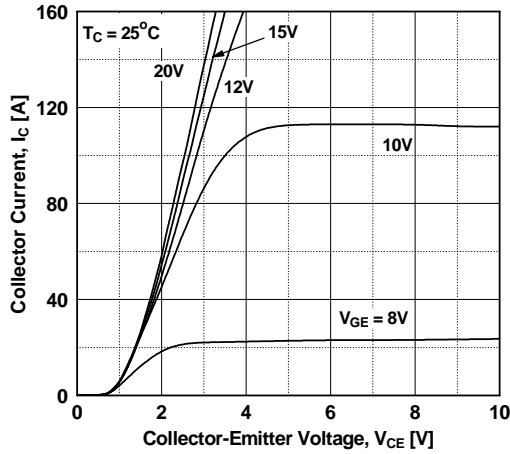


Figure 2. Typical Saturation Voltage Characteristics

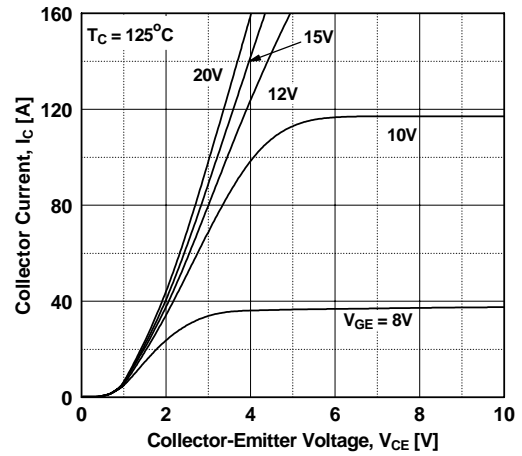


Figure 3. Typical Saturation Voltage Characteristics

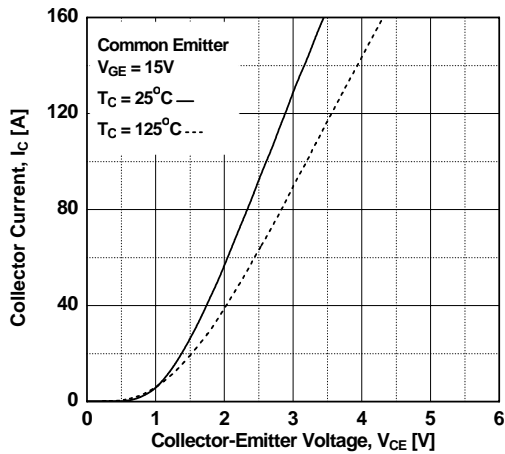


Figure 4. Transfer Characteristics

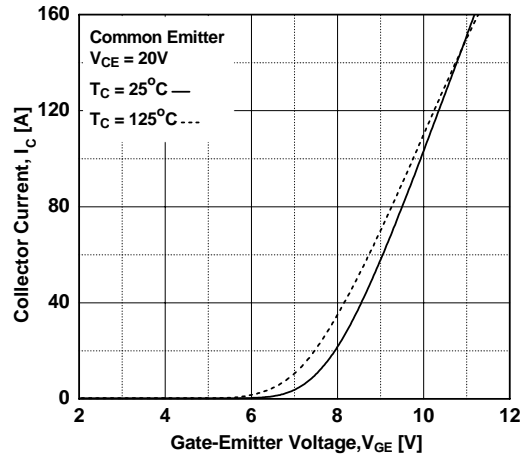


Figure 5. Saturation Voltage vs. Case

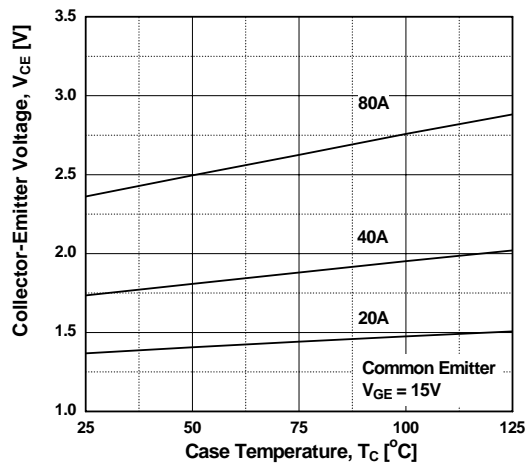
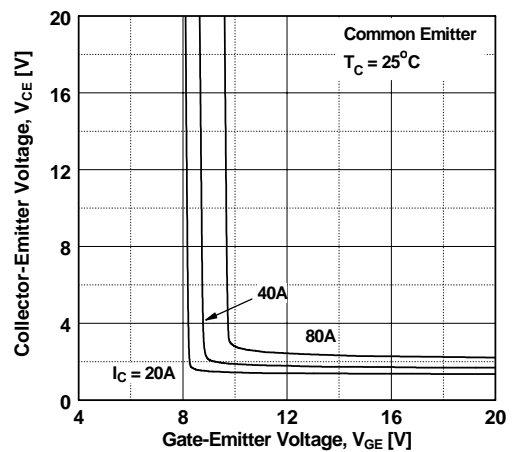
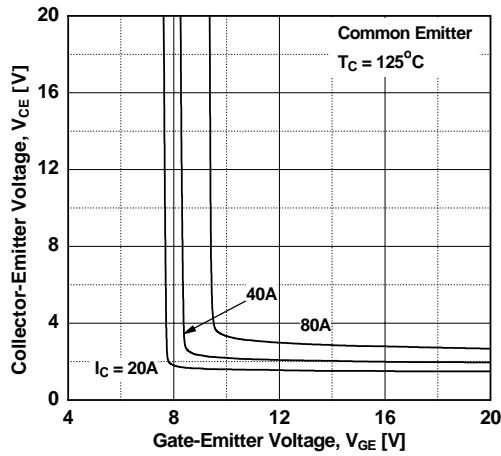


Figure 6. Saturation Voltage vs. Vge

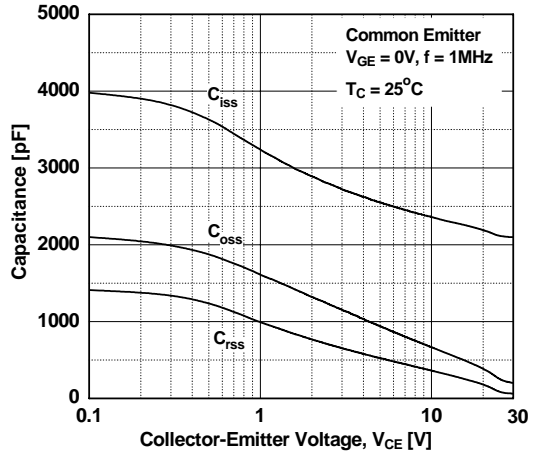


**Typical Performance Characteristics** (Continued)

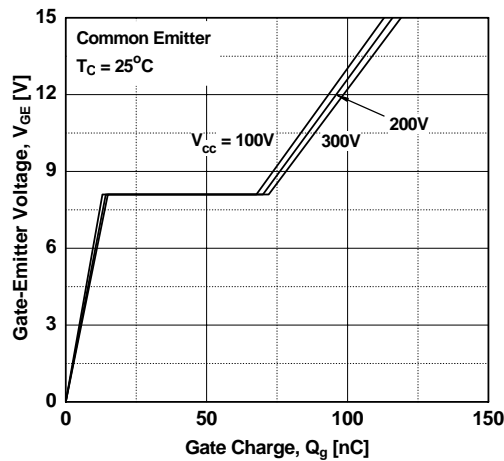
**Figure 7. Saturation Voltage vs. V<sub>GE</sub>**



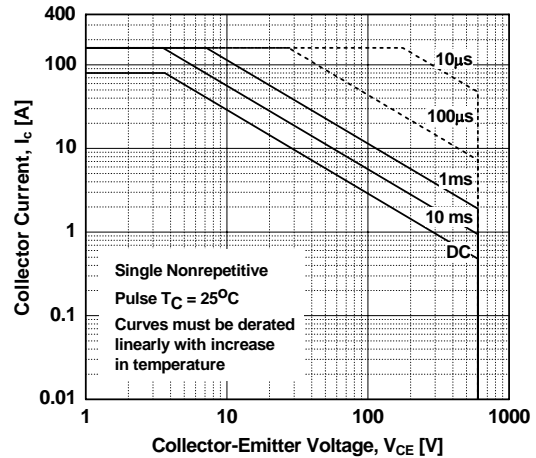
**Figure 8. Capacitance Characteristics**



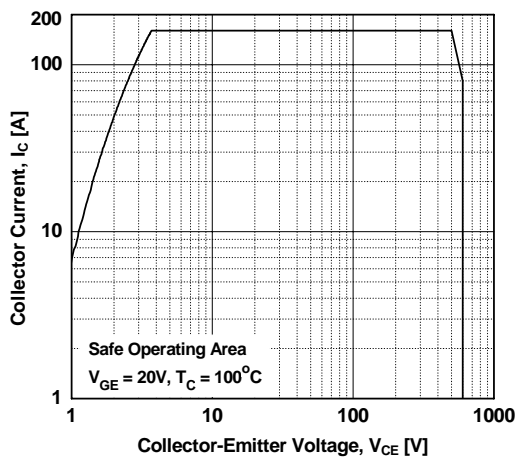
**Figure 9. Gate Charge Characteristics**



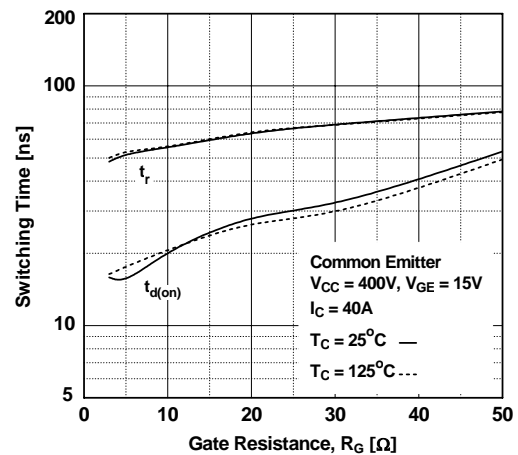
**Figure 10. SOA Characteristics**



**Figure 11. Turn-Off Switching SOA Characteristics**

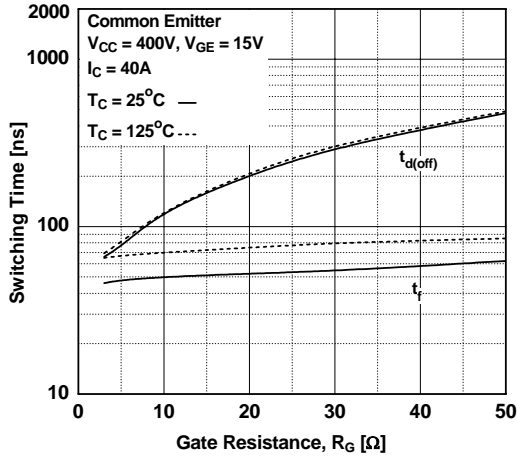


**Figure 12. Turn-On Characteristics vs. Gate Resistance**

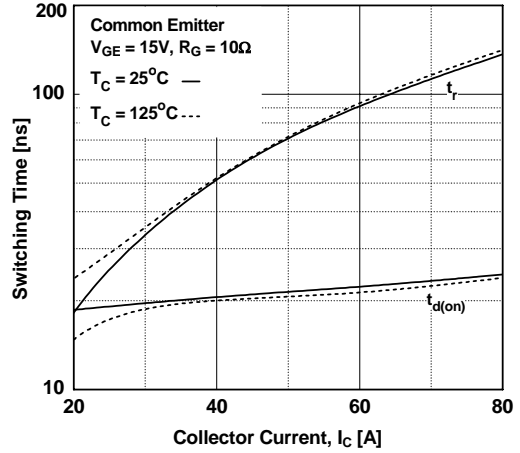


**Typical Performance Characteristics** (Continued)

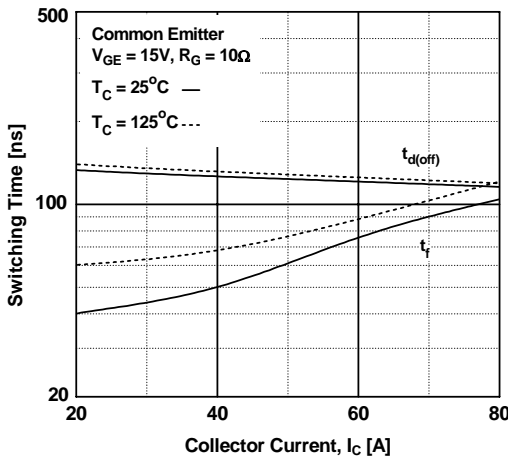
**Figure 13. Turn-Off Characteristics vs. Gate Resistance**



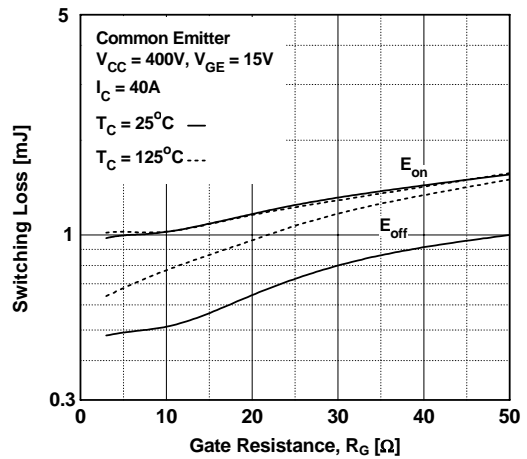
**Figure 14. Turn-On Characteristics vs. Collector Current**



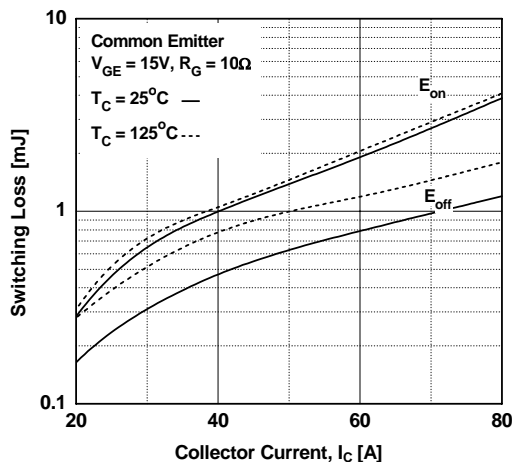
**Figure 15. Turn-Off Characteristics vs. Collector Current**



**Figure 16. Switching Loss vs Gate Resistance**

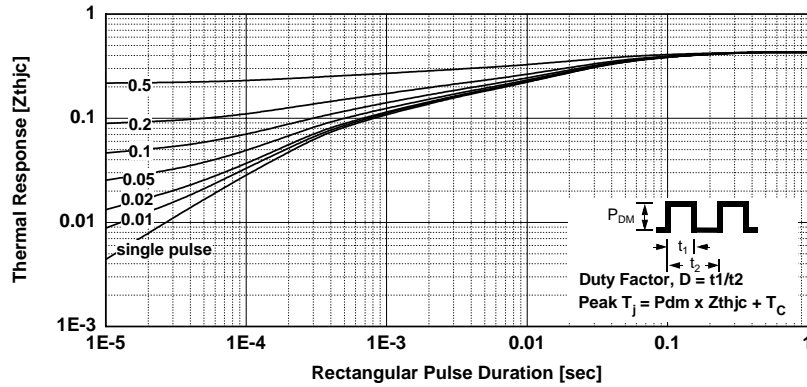


**Figure 17. Switching Loss vs Collector Current**

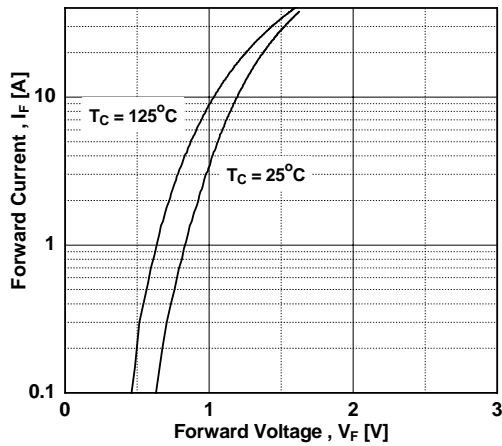


**Typical Performance Characteristics** (Continued)

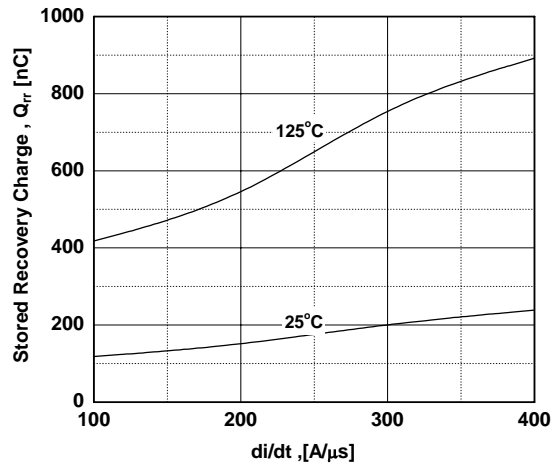
**Figure 18. Transient Thermal Impedance of IGBT**



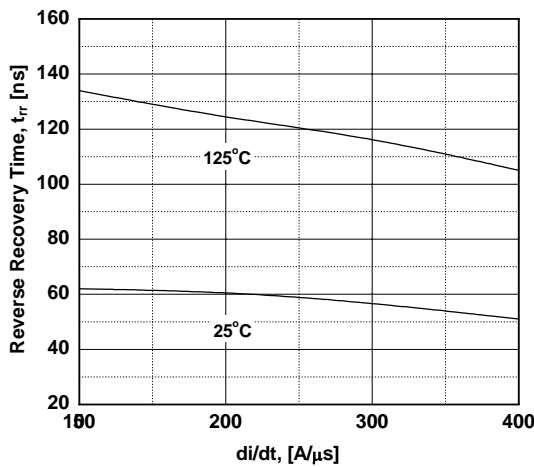
**Figure 19. Typical Forward Voltage Drop**



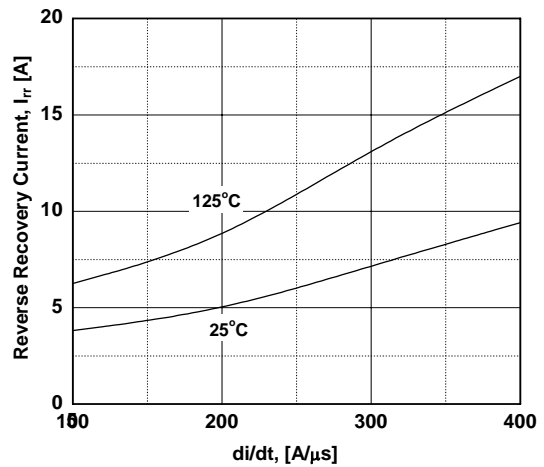
**Figure 20. Stored Charge**



**Figure 21. Reverse Recovery Time**

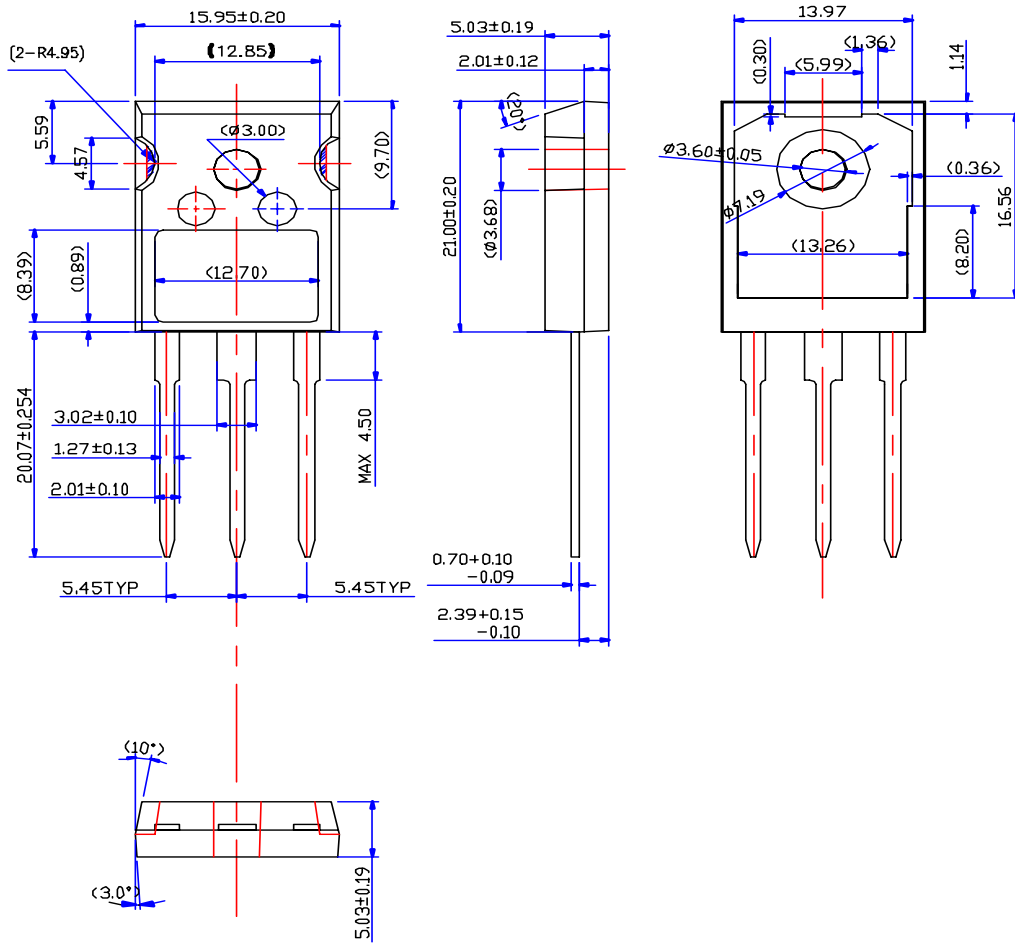


**Figure 22. Reverse Recovery Current**



Mechanical Dimensions

TO-247AD (FKS PKG CODE 001)









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